Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	44	(250/492.24).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 14:48
L2	0	(250/396).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 14:48
L3	2210	(250/492.1).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 14:48
L4	706	(250/492.22).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 14:48
L5	2741	(250/492.3).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/02/06 14:48
L6	5257	l1 or l3 or l4 or l5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 14:49
L7	27	pyroelectric near1 emit$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 15:07
L8	10	l7 and ((substrate or wafer or semiconductor) near3 (hold$3 or stage))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 15:13

L9	8	l8 and dielectric$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 15:15
L10	7	l9 and heat$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 15:15
L11	7	l10 and magnet$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 15:15
L12	2	l11 and (semiconduct$4 near4 film)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 15:06
L13	5	l11 and l6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 15:06
L14	2	(method with (fabricat$6 or manufactur$4 or mak$3) with (pyroelectric near1 emit$5))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 15:09
L15	5	((fabricat$6 or manufactur$4 or mak$3) with (pyroelectric near1 emit$5))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 15:08
L16	2	(method with (fabricat$6 or manufactur$4 or mak$3) with (pyroelectric near1 emit$5))".$clm."	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 15:09

L17	1	((pyroelectric near1 emit$5) with ((substrate or wafer or semiconductor) near3 (hold$3 or stage)) with dielectric$3 with heat$3 with magnet$4 with (semiconductor near2 film near4 dielectric$4))".$clm."	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 15:17
L18	4	(pyroelectric near2 plate) and (pattern$4 near2 (mask or reticle)) and ((prevent$3 or block$4) with electron)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/06 15:50
L19	0	(making or fabricat$4 or manufactur$4) with (pyroelectric near2 plate) with (pattern$4 near2 (mask or reticle)) with((prevent$3 or block$4) with electron)".$clm."	US-PGPUB	OR	ON	2006/02/06 15:51